

# MC74HCT244A

## Octal 3-State Noninverting Buffer/Line Driver/ Line Receiver with LSTTL-Compatible Inputs

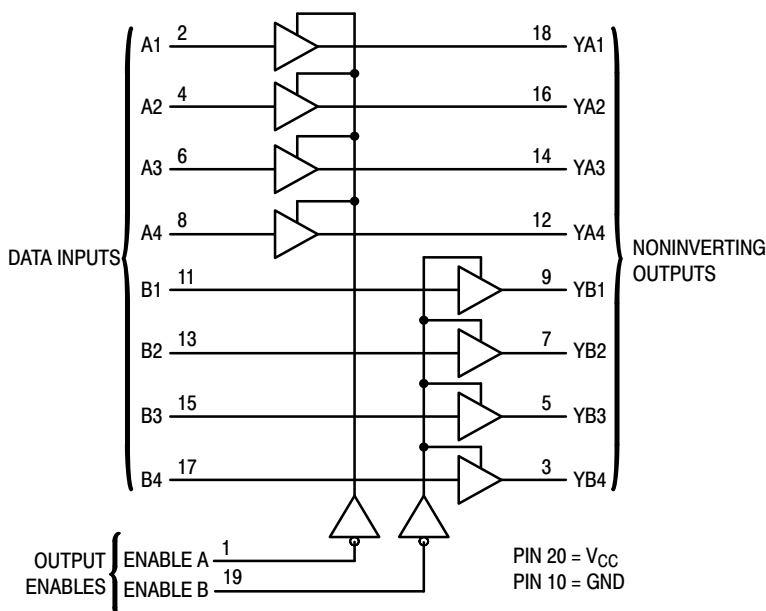
### High-Performance Silicon-Gate CMOS

The MC74HCT244A is identical in pinout to the LS244. This device may be used as a level converter for interfacing TTL or NMOS outputs to High-Speed CMOS inputs. The HCT244A is an octal noninverting buffer line driver line receiver designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The device has non-inverted outputs and two active-low output enables.

The HCT244A is the non-inverting version of the HCT240. See also HCT241.

#### Features

- Output Drive Capability: 15 LSTTL Loads
- TTL NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1  $\mu$ A
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 112 FETs or 28 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

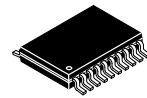


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SOIC-20W  
DW SUFFIX  
CASE 751D

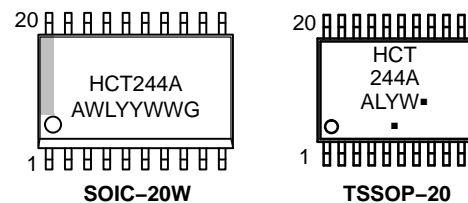


TSSOP-20  
DT SUFFIX  
CASE 948E

#### PIN ASSIGNMENT

ENABLE A	1	20	V <sub>CC</sub>
A1	2	19	ENABLE B
YB4	3	18	YA1
A2	4	17	B4
YB3	5	16	YA2
A3	6	15	B3
YB2	7	14	YA3
A4	8	13	B2
YB1	9	12	YA4
GND	10	11	B1

#### MARKING DIAGRAMS



A = Assembly Location  
WL, L = Wafer Lot  
YY, Y = Year  
WW, W = Work Week  
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### FUNCTION TABLE

Inputs		Outputs
Enable A, Enable B	A, B	YA, YB
L	L	L
L	H	H
H	X	Z

Z = high impedance, X = don't care

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

# MC74HCT244A

## MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	-0.5 to +7	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>in</sub>	DC Input Current, per Pin	±20	mA
I <sub>out</sub>	DC Output Current, per Pin	±35	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±75	mA
P <sub>D</sub>	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature, 1 mm from Case for 10 Seconds (SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>in</sub> and V<sub>out</sub> should be constrained to the range GND ≤ (V<sub>in</sub> or V<sub>out</sub>) ≤ V<sub>CC</sub>. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: -7 mW/°C from 65° to 125°C  
TSSOP Package: -6.1 mW/°C from 65° to 125°C

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 2)	0	500	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	Guaranteed Limit			Unit
				-55 to 25°C	≤ 85°C	≤ 125°C	
V <sub>IH</sub>	Minimum High-Level Input Voltage	V <sub>out</sub> = 0.1 V or V <sub>CC</sub> - 0.1 V  I <sub>out</sub>   ≤ 20 μA	4.5	2	2	2	V
			5.5	2	2	2	
V <sub>IL</sub>	Maximum Low-Level Input Voltage	V <sub>out</sub> = 0.1 V or V <sub>CC</sub> - 0.1 V  I <sub>out</sub>   ≤ 20 μA	4.5	0.8	0.8	0.8	V
			5.5	0.8	0.8	0.8	
V <sub>OH</sub>	Minimum High-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 20 μA	4.5	4.4	4.4	4.4	V
		V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 6 mA	4.5	3.98	3.84	3.7	
V <sub>OL</sub>	Maximum Low-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 20 μA	4.5	0.1	0.1	0.1	V
		V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 6 mA	4.5	0.26	0.33	0.4	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5	±0.1	±1.0	±1.0	μA
I <sub>oz</sub>	Maximum Three-State Leakage Current	Output in High-Impedance State V <sub>in</sub> = V <sub>IL</sub> or V <sub>IH</sub> ; V <sub>out</sub> = V <sub>CC</sub> or GND	5.5	±0.5	±5.0	±10	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	V <sub>in</sub> = V <sub>CC</sub> or GND I <sub>out</sub> = 0 μA	5.5	4	40	160	μA
ΔI <sub>CC</sub>	Additional Quiescent Supply Current	V <sub>in</sub> = 2.4 V, Any One Input V <sub>in</sub> = V <sub>CC</sub> or GND, Other Inputs I <sub>out</sub> = 0 μA	5.5	≥ -55°C	25°C to 125°C		mA
				2.9	2.4		

1. Total Supply Current = I<sub>CC</sub> + ΣΔI<sub>CC</sub>.

# MC74HCT244A

## AC ELECTRICAL CHARACTERISTICS ( $V_{CC} = 5.0 \text{ V} \pm 10\%$ , $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6 \text{ ns}$ )

Symbol	Parameter	Guaranteed Limit			Unit
		-55 to 25 °C	≤ 85 °C	≤ 125 °C	
$t_{PLH}$ , $t_{PHL}$	Maximum Propagation Delay, A to YA or B to YB (Figures 2 and 4)	20	25	30	ns
$t_{PLZ}$ , $t_{PHZ}$	Maximum Propagation Delay, Output Enable to YA or YB (Figures 3 and 5)	26	33	39	ns
$t_{PZL}$ , $t_{PZH}$	Maximum Propagation Delay, Output Enable to YA or YB (Figures 3 and 5)	22	28	33	ns
$t_{TLH}$ , $t_{THL}$	Maximum Output Transition Time, Any Output (Figures 2 and 4)	12	15	18	ns
$C_{in}$	Maximum Input Capacitance	10	10	10	pF
$C_{out}$	Maximum Three-State Output Capacitance (Output in High-Impedance State)	15	15	15	pF
$C_{PD}$	Power Dissipation Capacitance (Per Enabled Output)*	Typical @ 25°C, $V_{CC} = 5.0 \text{ V}$			pF
		55			

\* Used to determine the no-load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

### SWITCHING WAVEFORMS

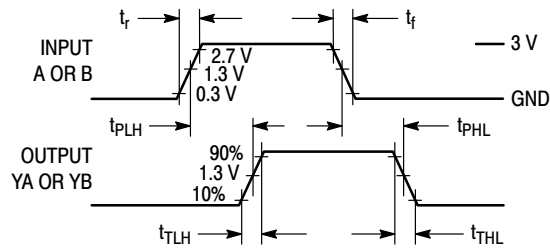


Figure 2.

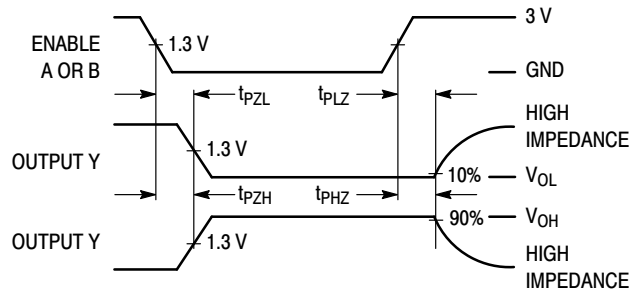
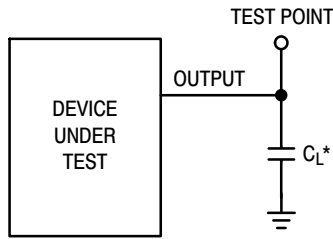


Figure 3.

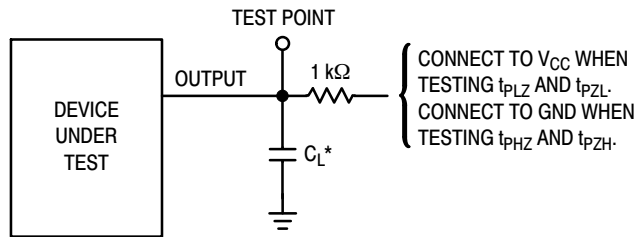
# MC74HCT244A

## TEST CIRCUITS



\*Includes all probe and jig capacitance

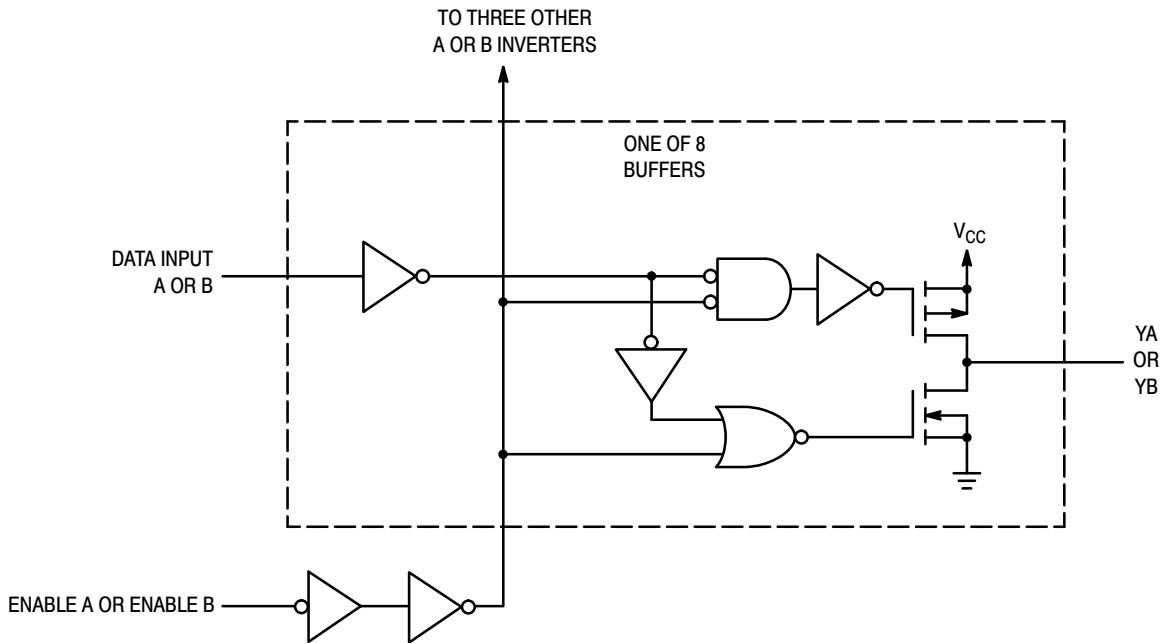
Figure 4.



\*Includes all probe and jig capacitance

Figure 5.

## LOGIC DETAIL



# MC74HCT244A

## ORDERING INFORMATION

Device	Package	Shipping†
MC74HCT244ADWG	SOIC-20 (Pb-Free)	38 Units / Rail
MC74HCT244ADWR2G	SOIC-20 (Pb-Free)	1000 / Tape & Reel
MC74HCT244ADTR2G	TSSOP-20 (Pb-Free)	2500 / Tape & Reel
NLVHCT244ADTR2G*	TSSOP-20 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1

SOIC-20 WB  
CASE 751D-05  
ISSUE H

DATE 22 APR 2015



NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS	
	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
b	0.35	0.49
c	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0°	7°

RECOMMENDED  
SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC  
MARKING DIAGRAM\*



- XXXXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- YY = Year
- WW = Work Week
- G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

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TSSOP-20 WB  
CASE 948E  
ISSUE D

DATE 17 FEB 2016

SCALE 2:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°



SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM\*



- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

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